

IN THE CLAIMS

Please amend the claims as follows.

1. (Currently Amended) A method of manufacturing a wafer assembly comprising a chip wafer onto which a cover wafer is deposited, the chip wafer comprising an active face and an inactive face, the active face comprising chip elements, the cover wafer being provided with a chip-element-receiving cavity located above a chip element, the method comprising the following steps:
 - a cover-wafer-depositing step, in which a the cover wafer is deposited on the active face so as to obtain a wafer assembly, the cover wafer being provided with a plurality of chip-receiving cavities, a chip-receiving cavity being located above a chip element, the cover wafer being made of an organic material; and
 - a wafer assembly thinning step, in which the inactive face of the chip wafer is thinned.
2. (Original) The method according to claim 1, wherein the method further comprises a chip-fixing step, in which a chip is fixed in a chip-receiving cavity.
3. (Currently Amended) The method according to claim 1, wherein the cover[[-]]wafer is made of a photosensitive material.
4. (Original) The method according to claim 3, wherein the photosensitive material comprises Benzo cyclo Butène.
5. (Original) The method according to claim 3, wherein the photosensitive material comprises a polyimide.
6. (Original) The method according to claim 3, wherein the photosensitive material comprises an epoxy-based material.
7. (Currently Amended) The method according to claim 2, wherein the method further comprises a wafer-assembly-cutting step, in which the wafer assembly is cut so as to obtain a plurality of chip assembly, a chip assembly comprising a the chip element onto which a chip is fixed.

8. (Currently Amended) The method according to claim 2 ~~or~~ 3, wherein the chip element[[s]] ~~are~~ is a GSM chip[[s]].
9. (Currently Amended) The method according to claim 2 ~~or~~ 3, wherein the chip[[s]] ~~are~~ is a RF chip[[s]].
10. (Currently Amended) The method according to claim 2 ~~or~~ 3, wherein the chip[[s]] ~~are~~ is a DPA chip[[s]].
11. (Currently Amended) Method of manufacturing a portable device comprising a support layer provided with a cavity, the method comprising:
 - a cover-wafer-depositing step, in which a cover wafer is deposited on an active face so as to obtain a wafer assembly, the cover wafer being provided with a plurality of chip-receiving cavities, a chip-receiving cavity being located above a chip element, the cover wafer being made of an organic material;
 - a wafer assembly thinning step, in which an inactive face of the chip wafer is thinned;
 - a chip-fixing step, in which a chip is fixed in a chip-receiving cavity;
 - a wafer-assembly-cutting step, in which the wafer assembly is cut so as to obtain a plurality of chip assembly, a chip assembly comprising the chip element onto which a chip is fixed; and
 - a chip-assembly-fixing step, in which [[a]]the chip[[-]]assembly according to claim 7 is fixed in the cavity.
12. (Currently Amended) A chip assembly ~~according to claim 7~~, comprising:
 - a chip wafer onto which a cover wafer is deposited,
 - wherein the chip wafer comprises an active face and an inactive face, and
 - wherein the active face comprises a plurality of chip elements;
 - a wafer assembly obtained when the cover wafer is deposited on the active face, wherein the wafer assembly is configured to be cut so as to obtain a plurality of chip assembly, the chip assembly comprising at least one of the plurality of chip elements onto which a chip is fixed; and
 - a chip-element-receiving cavity located above at least one of the plurality of chip elements on the cover wafer,
 - wherein the cover wafer is provided with a plurality of chip-receiving cavities,

wherein a chip-receiving cavity is located above at least one of the chip elements,
wherein the cover wafer is made of an organic material,
wherein the inactive face of the chip wafer is thinned, and
wherein the chip is fixed in the chip-receiving cavity.